

PHONE: (215) 631-9840 FAX: (215) 631-9855

MS1253

RF & MICROWAVE TRANSISTORS HF/VHF APPLICATIONS

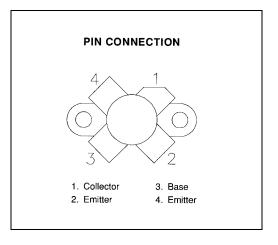
Features

- 50 MHz
- 12.5 VOLTS
- P_{OUT} = 70 WATTS
- G_p = 10 dB MINIMUM
- COMMON EMITTER CONFIGURATION

.380 4LFL (M113) epoxy sealed

DESCRIPTION:

The MS1253 is a 12.5 V Class C epitaxial silicon NPN transistor designed primarily for land mobile transmitter applications. This device utilizes emitter ballasting, is extremely stable and capable of withstanding high VSWR under operating conditions.



ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	45	V	
V _{CEO}	Collector-Emitter Voltage	18	V	
V _{EBO}	Emitter-Base Voltage	3.5	V	
P _{DISS}	Power Dissipation	183	W	
I c	Device Current	12.0	Α	
T J	Junction Temperature	200	°C	
T _{STG}	Storage Temperature	-65 to +150	°C	

Thermal Data

R _{TH(J-C)}	Thermal Resistance Junction-case	1.05	°C/W
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ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Cymphal		Toot Conditions		Value	l lni4		
Symbol		Test Conditions		n.	Тур.	Max.	Unit
BVcbo	I _C = 50 mA	I _E = 0 mA	4	5			V
BVces	I _C = 100 mA	V _{BE} = 0 V	4	0			V
BVebo	I _E = 10 mA	I _E = 0 mA	3.	5			V
BVceo	I _E = 50 mA	I _B = 0 mA	1	В			V
Ices	V _{CE} = 15 V	I _E = 0 mA		-		10	mA
H _{FE}	V _{CE} = 5 V	I _C = 5 A	1	0		200	

DYNAMIC

Symbol		Test Conditions		Value			Unit	
Syllibol	rest Conditions		Min.	Тур.	Max.	Offic		
P _{out}	f = 50 MHz	P _{IN} = 7W	V _{CE} = 12.5V	70			W	
G _{PE}	f = 50 MHz	$P_{IN} = 7W$	$V_{CE} = 12.5V$	10			dB	
ης	f = 50 MHz	$P_{IN} = 7W$	$V_{CE} = 12.5V$	45			%	
Сов	f = 1 MHz	$V_{CB} = 12.5 \text{ V}$				300	pf	

IMPENDANCE DATA

FREQ	$Z_IN(\Omega)$	$Z_{\mathtt{CL}}(\Omega)$
50 MHz	0.8 + j0.9	1.2 + j0.6

 $P_{OUT} = 70W$ $V_{CF} = 12.5V$



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PACKAGE MECHANICAL DATA

